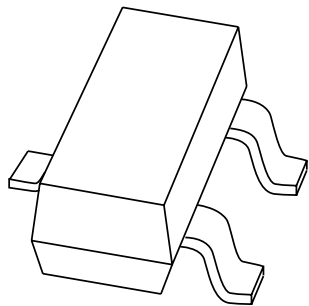


# DATA SHEET



## **MMBT3906** PNP switching transistor

Product specification  
Supersedes data of 2000 Apr 11

2003 Mar 18

# PNP switching transistor

# MMBT3906

### FEATURES

- Collector current capability  $I_C = -200$  mA
- Collector-emitter voltage  $V_{CEO} = -40$  V.

### APPLICATIONS

- General switching and amplification.

### DESCRIPTION

PNP switching transistor in a SOT23 plastic package.  
NPN complement: MMBT3904.

### MARKING

TYPE NUMBER	MARKING CODE <sup>(1)</sup>
MMBT3906	7B*

### Note

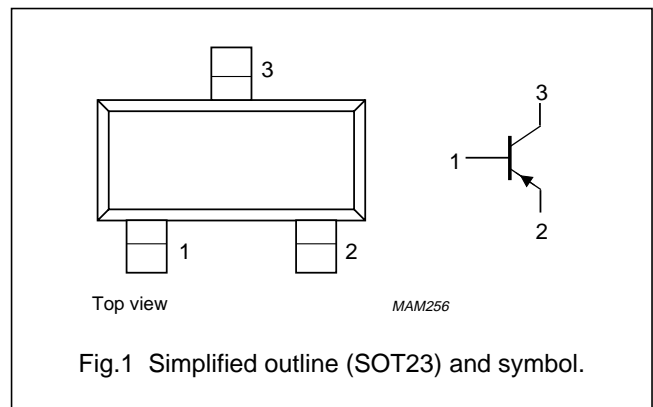
- \* = p: Made in Hong Kong.  
\* = t: Made in Malaysia.  
\* = W: Made in China.

### QUICK REFERENCE DATA

SYMBOL	PARAMETER	MAX.	UNIT
$V_{CEO}$	collector-emitter voltage	-40	V
$I_C$	collector current (DC)	-200	mA

### PINNING

PIN	DESCRIPTION
1	base
2	emitter
3	collector



### LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 60134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
$V_{CBO}$	collector-base voltage	open emitter	-	-40	V
$V_{CEO}$	collector-emitter voltage	open base	-	-40	V
$V_{EBO}$	emitter-base voltage	open collector	-	-6	V
$I_C$	collector current (DC)		-	-200	mA
$I_{CM}$	peak collector current		-	-200	mA
$I_{BM}$	peak base current		-	-100	mA
$P_{tot}$	total power dissipation	$T_{amb} \leq 25$ °C; note 1	-	250	mW
$T_{stg}$	storage temperature		-65	+150	°C
$T_j$	junction temperature		-	150	°C
$T_{amb}$	operating ambient temperature		-65	+150	°C

### Note

1. Transistor mounted on an FR4 printed-circuit board.

## PNP switching transistor

## MMBT3906

## THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
$R_{th\ j-a}$	thermal resistance from junction to ambient	note 1	500	K/W

## Note

1. Transistor mounted on an FR4 printed-circuit board.

## CHARACTERISTICS

$T_{amb} = 25\text{ }^{\circ}\text{C}$  unless otherwise specified.

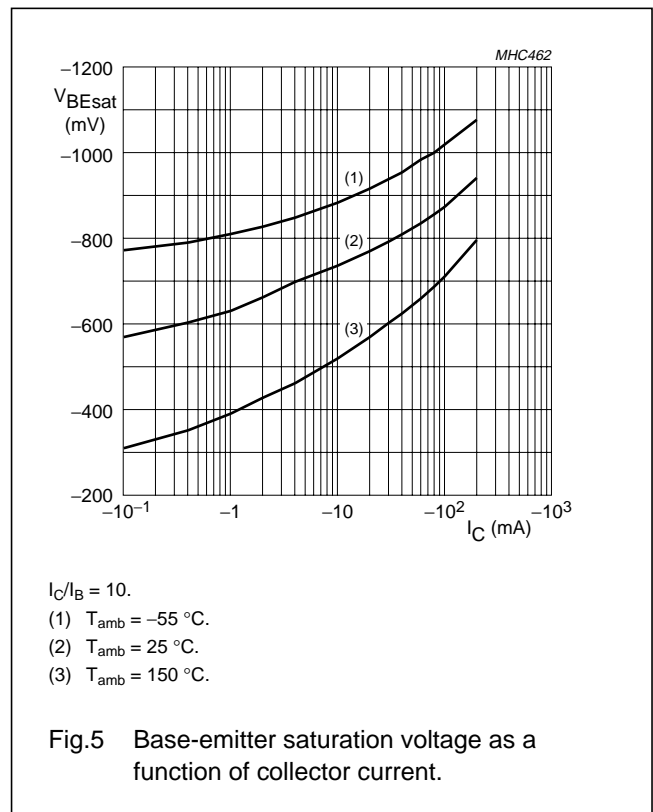
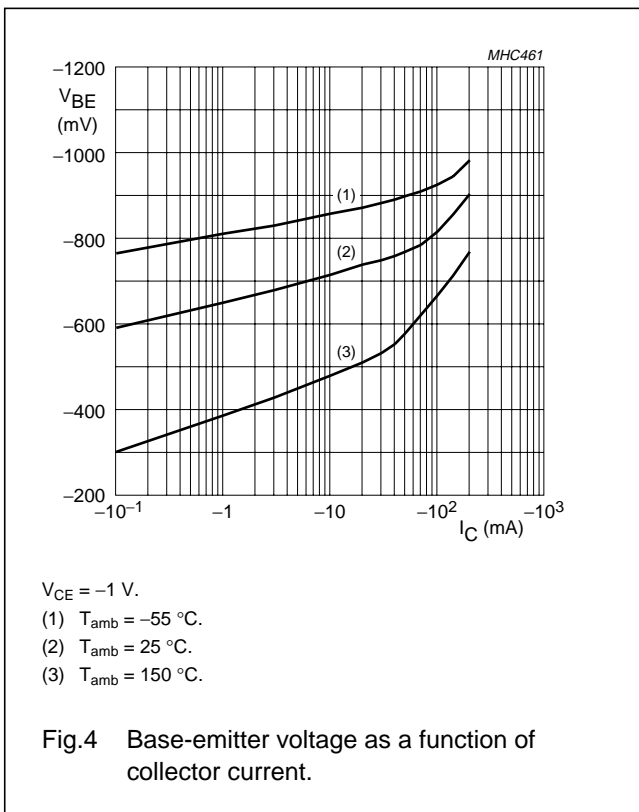
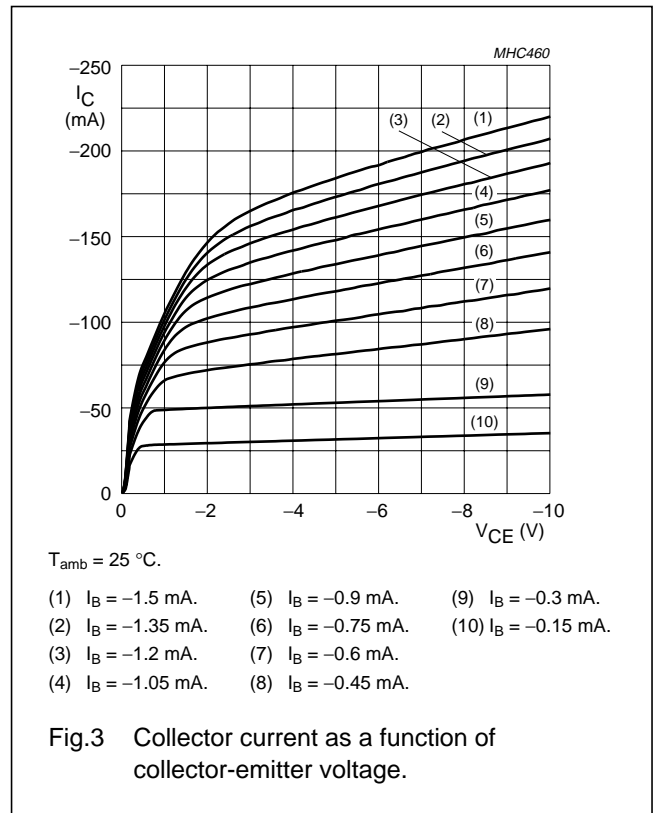
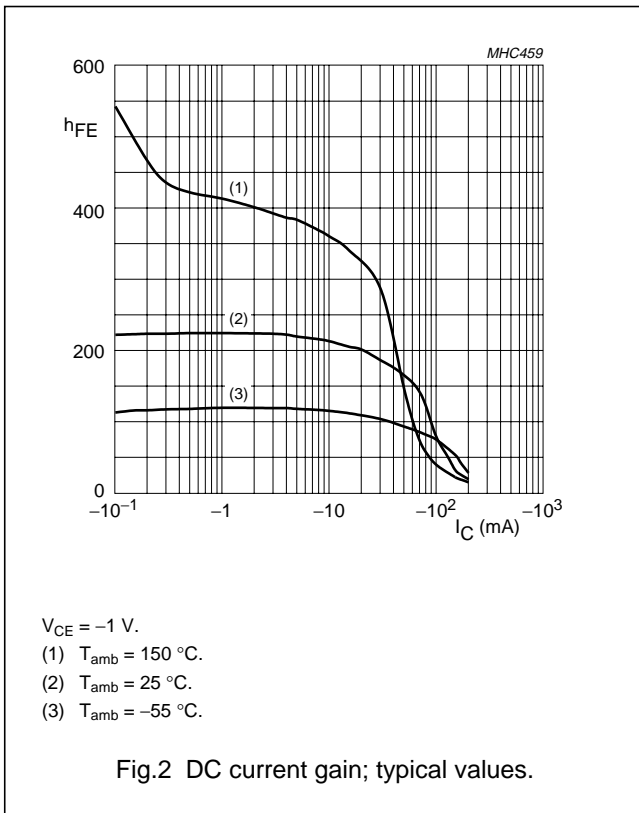
SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
$I_{CBO}$	collector cut-off current	$I_E = 0; V_{CB} = -30\text{ V}$	–	–50	nA
$I_{EBO}$	emitter cut-off current	$I_C = 0; V_{EB} = -6\text{ V}$	–	–50	nA
$h_{FE}$	DC current gain	$V_{CE} = -1\text{ V}$ ; see Fig.2 $I_C = -0.1\text{ mA}$ $I_C = -1\text{ mA}$ $I_C = -10\text{ mA}$ $I_C = -50\text{ mA}$ $I_C = -100\text{ mA}$	60 80 100 60 30	– – 300 – –	
$V_{CEsat}$	collector-emitter saturation voltage	$I_C = -10\text{ mA}; I_B = -1\text{ mA}$	–	–250	mV
		$I_C = -50\text{ mA}; I_B = -5\text{ mA}$	–	–400	mV
$V_{BEsat}$	base-emitter saturation voltage	$I_C = -10\text{ mA}; I_B = -1\text{ mA}$	–	–850	mV
		$I_C = -50\text{ mA}; I_B = -5\text{ mA}$	–	–950	mV
$C_c$	collector capacitance	$I_E = i_e = 0; V_{CB} = -5\text{ V}; f = 1\text{ MHz}$	–	4.5	pF
$C_e$	emitter capacitance	$I_C = i_c = 0; V_{EB} = -500\text{ mV}; f = 1\text{ MHz}$	–	10	pF
$f_T$	transition frequency	$I_C = -10\text{ mA}; V_{CE} = -20\text{ V}; f = 100\text{ MHz}$	250	–	MHz
F	noise figure	$I_C = -100\text{ }\mu\text{A}; V_{CE} = -5\text{ V}; R_S = 1\text{ k}\Omega; f = 10\text{ Hz to }15.7\text{ kHz}$	–	4	dB

## Switching times (between 10% and 90% levels); see Fig.7

$t_d$	delay time	$I_{Con} = -10\text{ mA}; I_{Bon} = -1\text{ mA}; I_{Boff} = 1\text{ mA}$	–	35	ns
$t_r$	rise time		–	35	ns
$t_s$	storage time		–	225	ns
$t_f$	fall time		–	75	ns

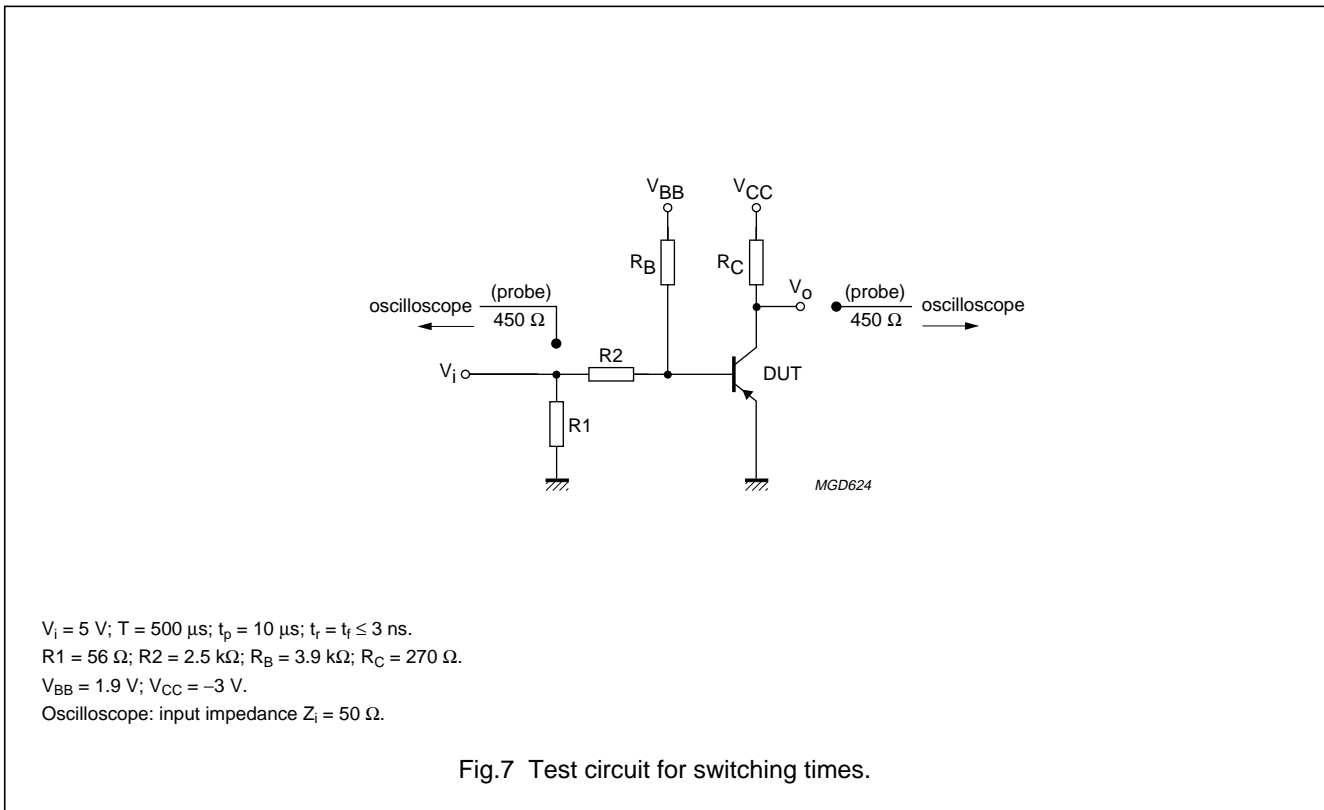
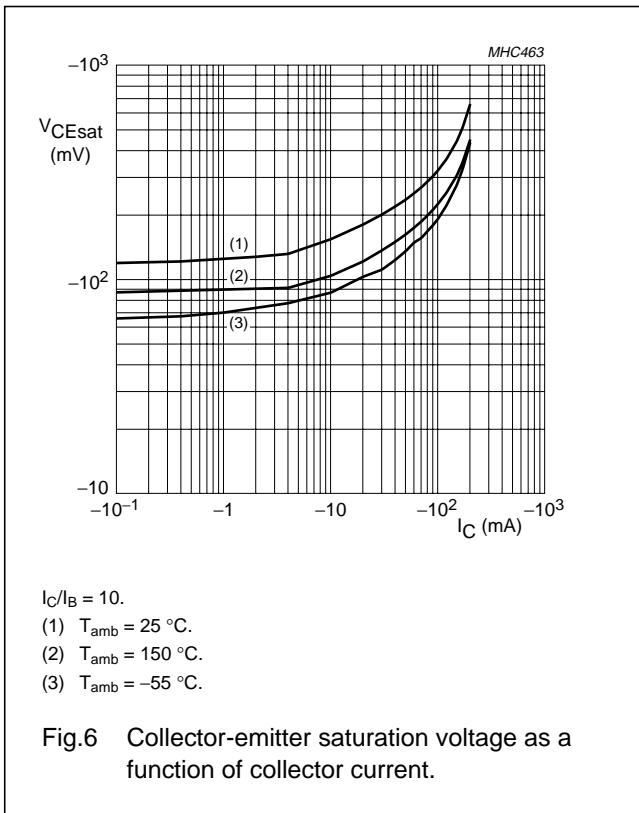
PNP switching transistor

MMBT3906



PNP switching transistor

MMBT3906



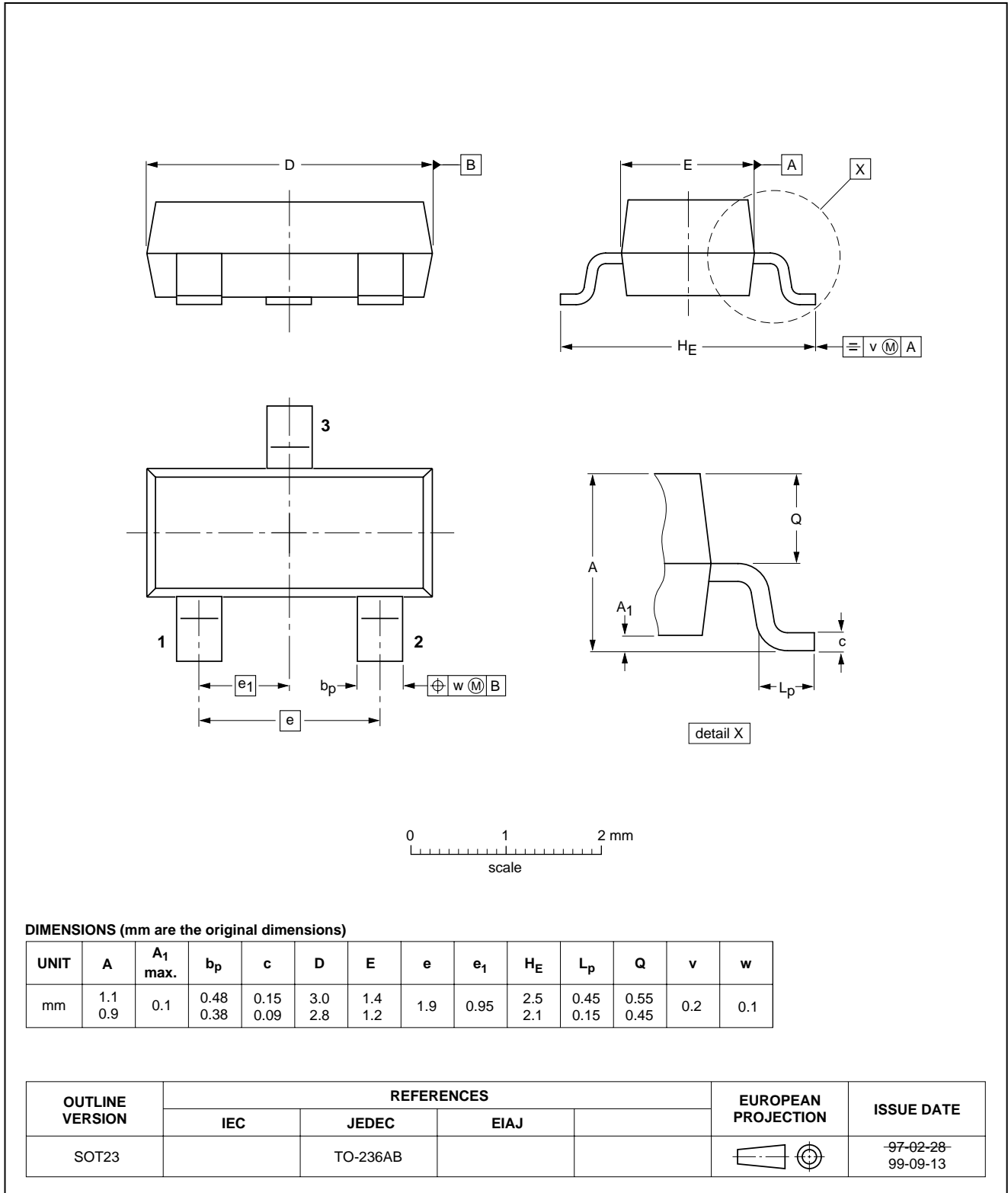
PNP switching transistor

MMBT3906

PACKAGE OUTLINE

Plastic surface mounted package; 3 leads

SOT23



## PNP switching transistor

MMBT3906

## DATA SHEET STATUS

LEVEL	DATA SHEET STATUS <sup>(1)</sup>	PRODUCT STATUS <sup>(2)(3)</sup>	DEFINITION
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